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## FDA24N40F N-Channel UniFET<sup>TM</sup> FRFET<sup>®</sup> MOSFET 400 V, 23 A, 190 mΩ

#### Features

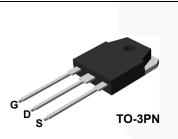
- $R_{DS(on)}$  = 150 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 11.5 A
- Low Gate Charge (Typ. 46 nC)
- Low C<sub>rss</sub> (Typ. 25 pF)
- 100% Avalanche Tested
- RoHS Compliant

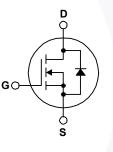
#### Applications

- Uninterruptible Power Supply
- AC-DC Power Supply

### Description

UniFET<sup>™</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. The body diode's reverse recovery performance of UniFET FRFET<sup>®</sup> MOSFET has been enhanced by lifetime control. Its tri is less than 100nsec and the reverse dv/dt immunity is 15V/ns while normal planar MOSFETs have over 200nsec and 4.5V/nsec respectively. Therefore, it can remove additional component and improve system reliability in certain applications in which the performance of MOSFET's body diode is significant. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp balasts.





#### MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		FDA24N40F	Unit			
V <sub>DSS</sub>	Drain to Source Voltage	400	V			
V <sub>GSS</sub>	Gate to Source Voltage			±30	V	
ID	Drain Current	- Continuous (T <sub>C</sub> = 25 <sup>o</sup> C)		23		
	Drain Current	- Continuous (T <sub>C</sub> = 100 <sup>o</sup> C)		13.8	A	
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	92	А	
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)			1190	mJ	
I <sub>AR</sub>	Avalanche Current		(Note 1)	23	А	
E <sub>AR</sub>	Repetitive Avalanche Ener	ду	(Note 1)	23.5	mJ	
dv/dt	Peak Diode Recovery dv/c	(Note 3)	4.5	V/ns		
P <sub>D</sub>	Dewer Dissinction	(T <sub>C</sub> = 25°C)		235	W	
	Power Dissipation	- Derate Above 25°C		1.8	W/ºC	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C	
T <sub>I</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C	

#### Thermal Characteristics

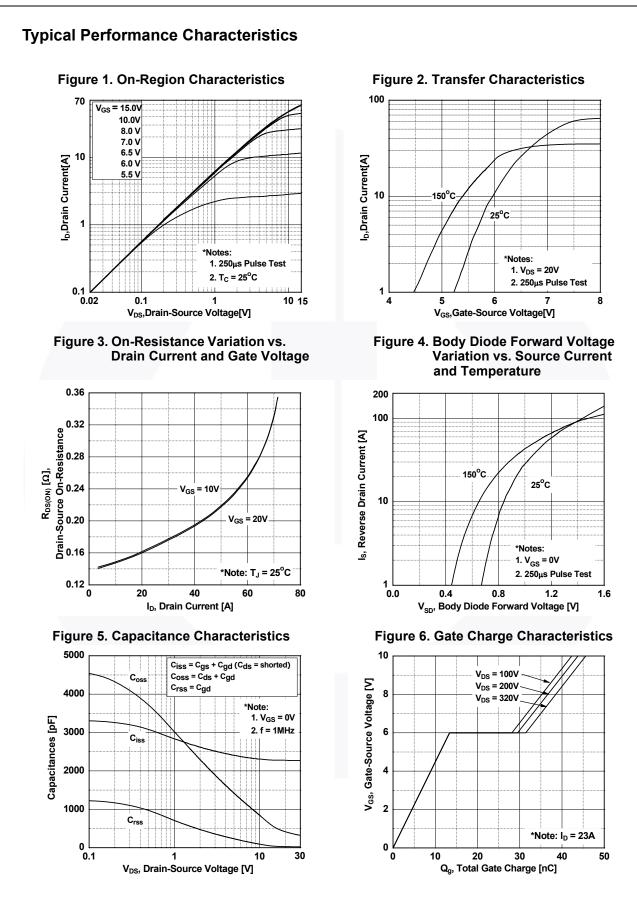
Symbol	Parameter	FDA24N40F	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.53	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	40	C/VV

May 2014

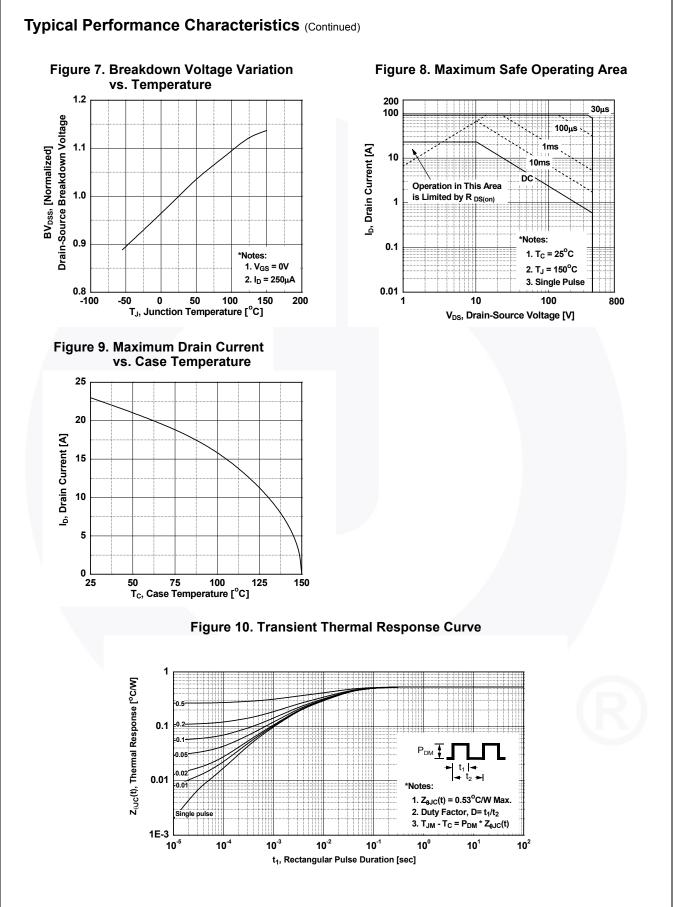
		Top Mark	Package	Packing Method	Reel Size	e Ta	ape Width	Qu	antity
		TO-3PN			N/A		30 units		
Electrical	Chara	acteristics $T_C = 25^{\circ}C$	unless othe	erwise noted.					
Symbol		Parameter		Test Condition	S	Min.	Тур.	Max.	Unit
Off Charac	teristics								
BV <sub>DSS</sub>	Drain to	Source Breakdown Voltage		I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 25 <sup>o</sup> C		400	_	-	V
∆BV <sub>DSS</sub>		wn Voltage Temperature				400			
$/\Delta T_J$	Coefficient $I_D = 250 \ \mu$ A, Referenced to $25^{\circ}$ C		to 25°C	-	0.5	-	V/ºC		
I <sub>DSS</sub>	Zero Gate Voltage Drain Current			$V_{DS} = 400 V, V_{GS} = 0 V$ $V_{DS} = 320 V, T_{C} = 125^{o}C$		-	-	10	μA
'DSS						-	-	100	μι
I <sub>GSS</sub>	Gate to Body Leakage Current $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			-	-	±100	nA		
On Charact	teristics								
V <sub>GS(th)</sub>	Gate Thr	eshold Voltage	VG	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA		3.0	-	5.0	V
R <sub>DS(on)</sub>	Static Dr	ain to Source On Resistance		$V_{GS} = 10 V, I_D = 11.5 A$		-	0.15	0.19	Ω
9 <sub>FS</sub>	Forward	Transconductance		<sub>S</sub> = 20 V, I <sub>D</sub> = 11.5 A		-	29	-	S
Dynamic C	haracte	ristics					1 1		
C <sub>iss</sub>	1	pacitance				-	2280	3030	pF
C <sub>oss</sub>		apacitance		V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,		-	370	490	pF
C <sub>rss</sub>		Transfer Capacitance	f =	1 MHz	-	-	25	38	pF
Q <sub>g(tot)</sub>		te Charge at 10V	V-	<sub>S</sub> = 320 V, I <sub>D</sub> = 23 A,		-	46	60	nC
Q <sub>gs</sub>	Gate to S	Source Gate Charge		$V_{\rm GS} = 320$ V, $T_{\rm D} = 23$ A, $V_{\rm GS} = 10$ V (Note 4)		-	13	-	nC
Q <sub>gd</sub>	Gate to D	Drain "Miller" Charge				-	18	-	nC
Switching	Charact	eristics	·						
t <sub>d(on)</sub>	1	Delay Time		$V_{DS} = 200 \text{ V}, \text{ I}_{D} = 23 \text{ A},$ $V_{GS} = 10 \text{ V}, \text{ R}_{G} = 25 \Omega $ (Note 4)		-	40	90	ns
t <sub>r</sub>		Rise Time	VD			-	92	195	ns
t <sub>d(off)</sub>	Turn-Off	Delay Time				-	120	250	ns
t <sub>f</sub>	Turn-Off	Fall Time				-	75	160	ns
Drain-Sour	ce Diod	e Characteristics	H				1		1
I <sub>S</sub>		Continuous Drain to Source	e Diode Foi	ward Current			_	23	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current				-	-	92	Α	
V <sub>SD</sub>	Drain to Source Diode Forward Voltage		1	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 23 A		-	-	1.5	V
t <sub>rr</sub>	Reverse	e Recovery Time		$V_{GS} = 0 V, I_{SD} = 23 A,$		-	110		ns
	-	Reverse Recovery Charge		dl <sub>F</sub> /dt = 100 A/μs		-	0.3	· _ · ·	μC

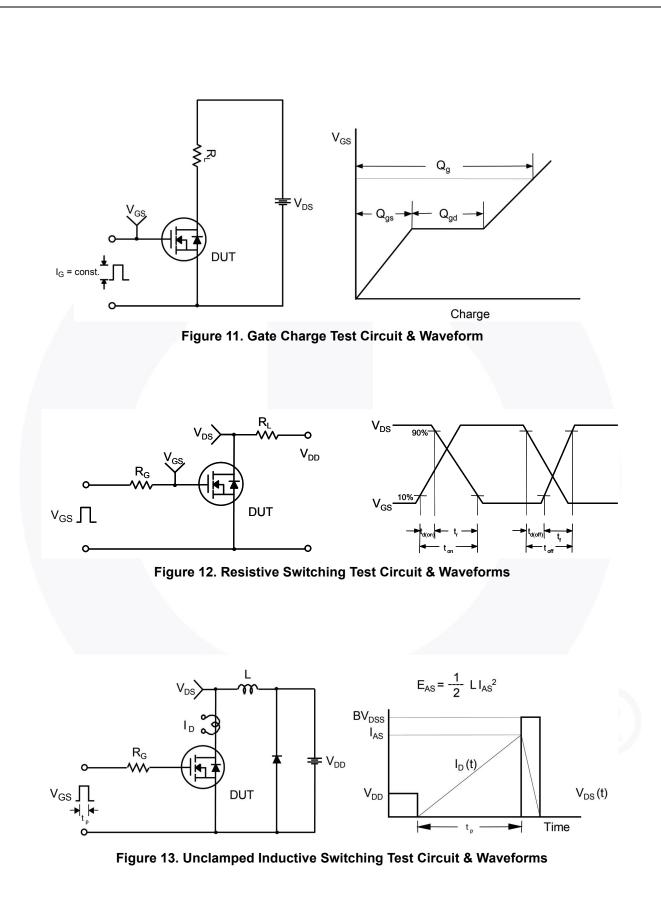
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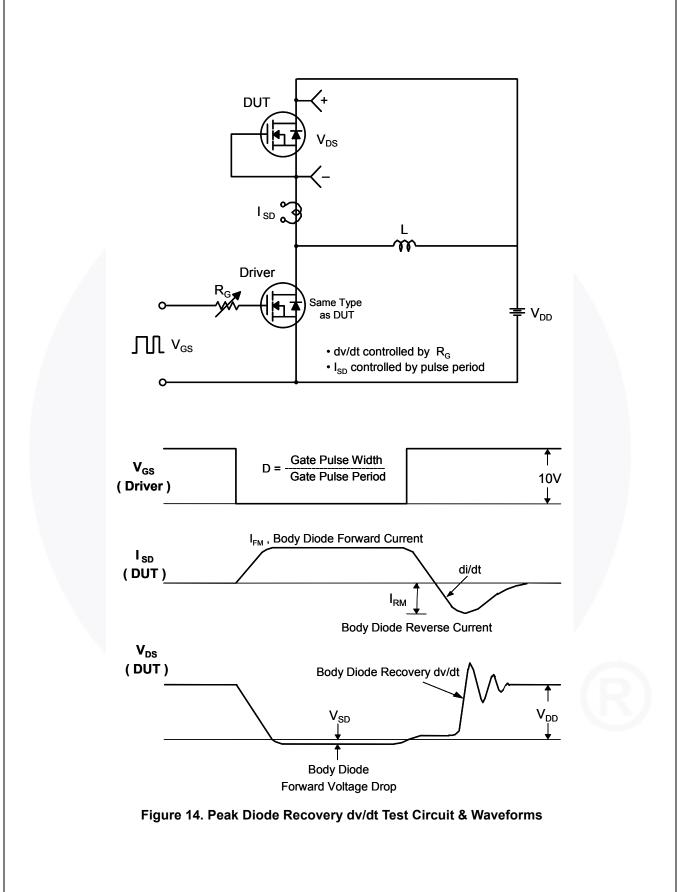


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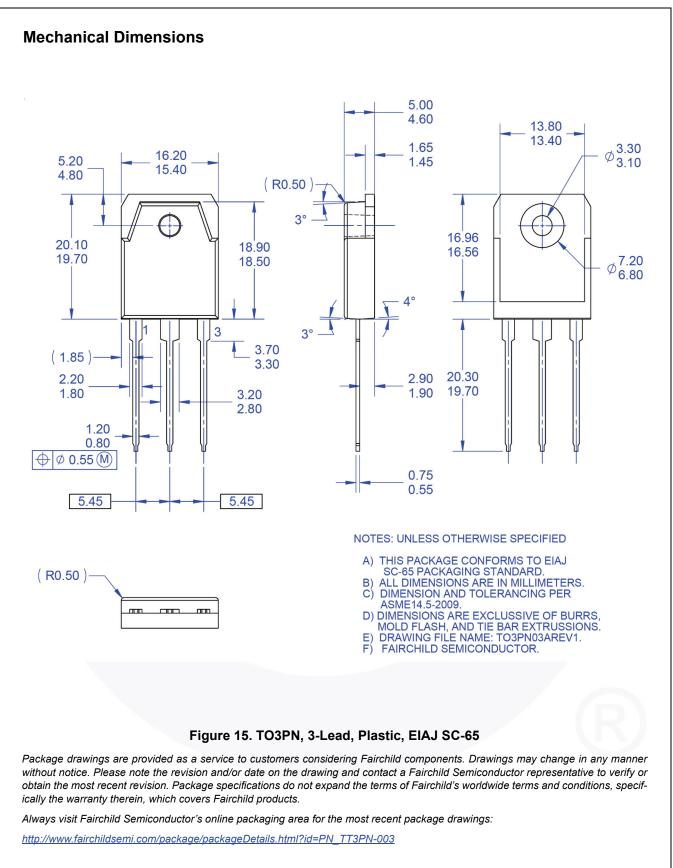




FDA24N40F — N-Channel UniFET<sup>TM</sup> FRFET<sup>®</sup> MOSFET



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